# CoolMOS® Power Transistor

Features

- Lowest figure-of-merit $R_{ON}xQ_g$

- Ultra low gate charge

- Extreme dv/dt rated

- High peak current capability

- Qualified for industrial grade applications according to JEDEC[1]

- Pb-free lead plating; RoHS compliant; Halogen free mold compound

CoolMOS CP is designed for:

- Hard switching topologies for Server and Telecom

Product Summary

V_{DS} @ $T_{j,max}$	650	V
$R_{DS(on),max}$	0.165	Ω
$Q_{g,typ}$	39	nC

PG-TO262

drain pin 2
gate pin 1
source pin 3
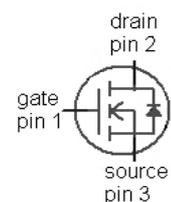
Type	Package	Marking
IPI60R165CP	PG-TO262	6R165P

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C	21	A
		T_C=100 °C	13	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25 °C	61	
Avalanche energy, single pulse	E_{AS}	I_D=7.9 A, V_{DD}=50 V	522	mJ
Avalanche energy, repetitive t_{AR}[2],[3]	E_{AR}	I_D=7.9 A, V_{DD}=50 V	0.79	
Avalanche current, repetitive t_{AR}[2],[3]	I_{AR}		7.9	A
MOSFET dv/dt ruggedness	dv/dt	V_{DS}=0...480 V	50	V/ns
Gate source voltage	V_{GS}	static	±20	V
		AC (f>1 Hz)	±30	
Power dissipation	P_{tot}	T_C=25 °C	192	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	°C

Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	T_C=25 °C	12	A
Diode pulse current[2]	$I_{S,pulse}$		61	
Reverse diode dv/dt[4]	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	-	0.65	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250 µA	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.79 mA	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	V_{DS}=600 V, V_{GS}=0 V, T_j=25 °C	-	-	1	µA
		V_{DS}=600 V, V_{GS}=0 V, T_j=150 °C	-	10	-	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=12 A, T_j=25 °C	-	0.15	0.165	Ω
		V_{GS}=10 V, I_D=12 A, T_j=150 °C	-	0.40	-	
Gate resistance	R_G	f=1 MHz, open drain	-	1.9	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=100 V, f=1 MHz	-	2000	-	pF
Output capacitance	C_{oss}		-	100	-	
Effective output capacitance, energy related [4)]	$C_{o(er)}$	V_{GS}=0 V, V_{DS}=0 V to 480 V	-	83	-	
Effective output capacitance, time related [5)]	$C_{o(tr)}$		-	220	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=400 V, V_{GS}=10 V, I_D=12 A, R_G=3.3 Ω	-	12	-	ns
Rise time	t_r		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	50	-	
Fall time	t_f		-	5	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=400 V, I_D=12 A, V_{GS}=0 to 10 V	-	9	-	nC
Gate to drain charge	Q_{gd}		-	13.0	-	
Gate charge total	Q_g		-	39	52	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	V
Reverse Diode						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=12 A, T_j=25 °C	-	0.9	1.2	V
Reverse recovery time	t_{rr}	V_R=400 V, I_F=I_S, di_F/dt=100 A/µs	-	390	-	ns
Reverse recovery charge	Q_{rr}		-	7.5	-	µC
Peak reverse recovery current	I_{rrm}		-	38	-	A

[1)] J-STD20 and JESD22

[2)] Pulse width t_p limited by $T_{j,max}$

[3)] Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR}*f$.

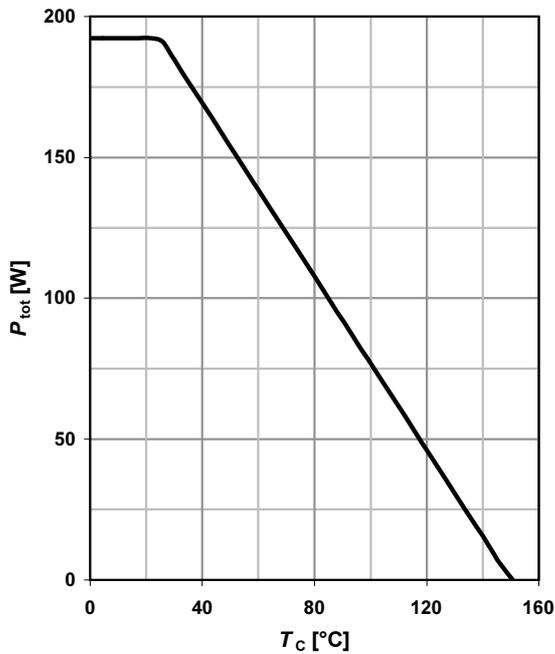[4)] $I_{SD}≤I_D$, di/dt≤200A/µs, V_{DClink}=400V, $V_{peak}<V_{(BR)DSS}$, $T_j<T_{jmax}$, identical low side and high side switch.

[4)] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

[5)] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
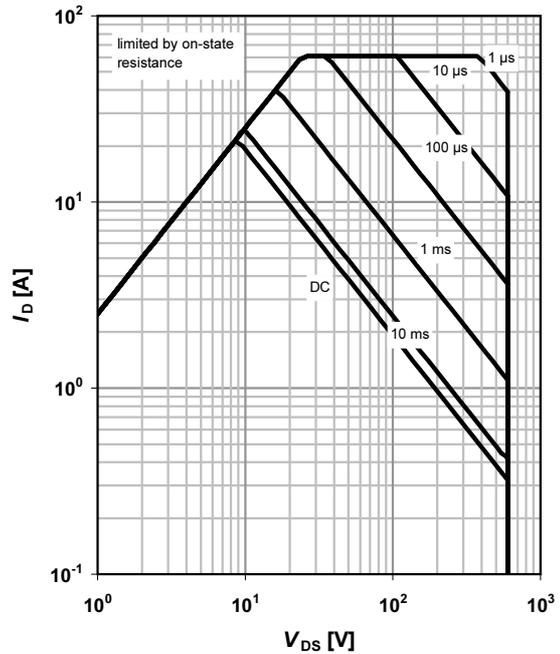
1 Power dissipation

P_{tot}=f(T_C)

2 Safe operating area
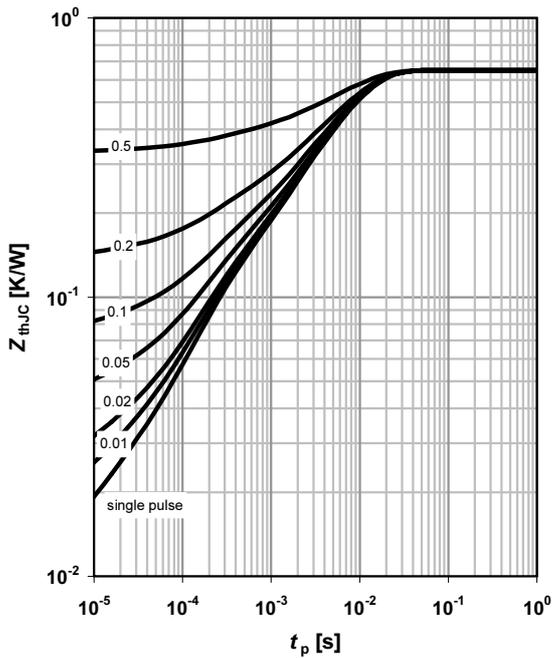
I_D=f(V_{DS}); T_C=25 °C; D=0

parameter: t_p

3 Max. transient thermal impedance

Z_{thJC}=f(t_p)
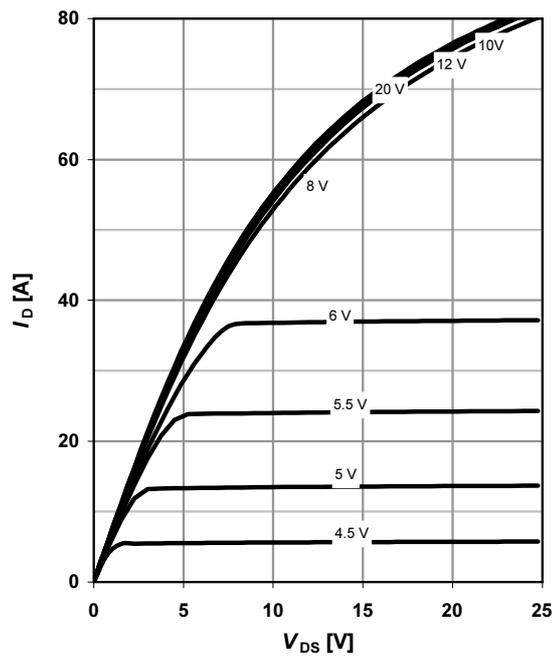
parameter: D=t_p/T

4 Typ. output characteristics
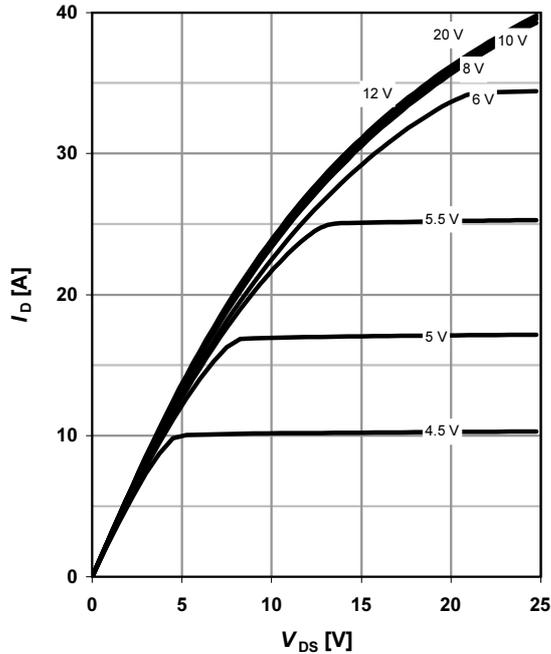
I_D=f(V_{DS}); T_j=25 °C

parameter: V_{GS}

5 Typ. output characteristics

I_D=f(V_{DS}); T_j=150 °C

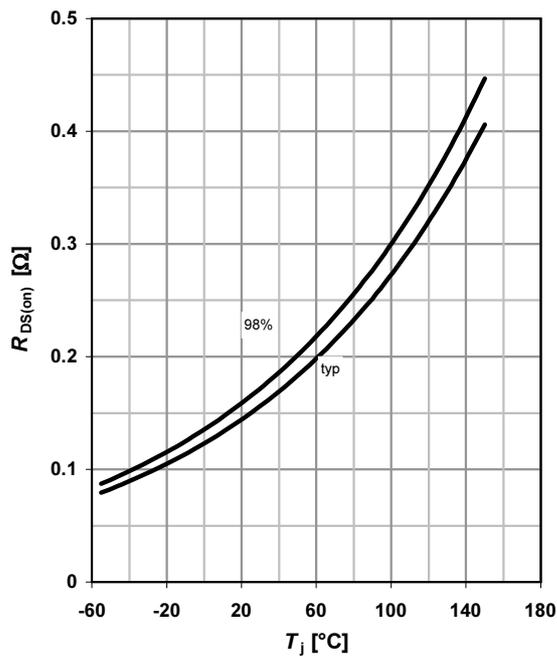parameter: V_{GS}

6 Typ. drain-source on-state resistance

$R_{DS(on)}$=f(I_D); T_j=150 °C

parameter: V_{GS}
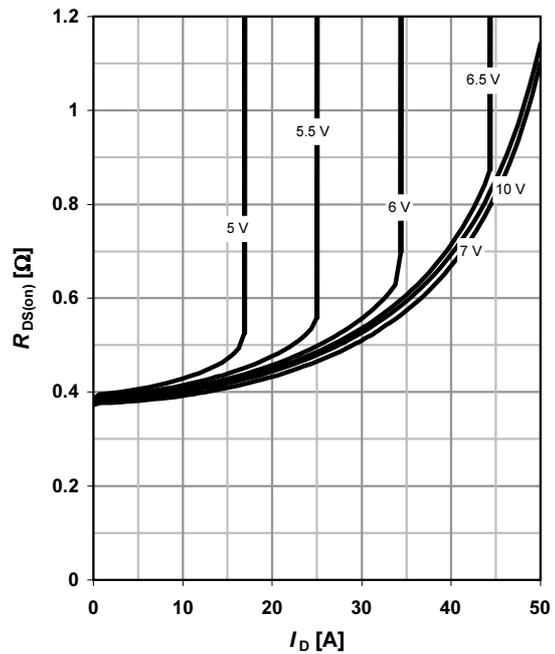
7 Drain-source on-state resistance

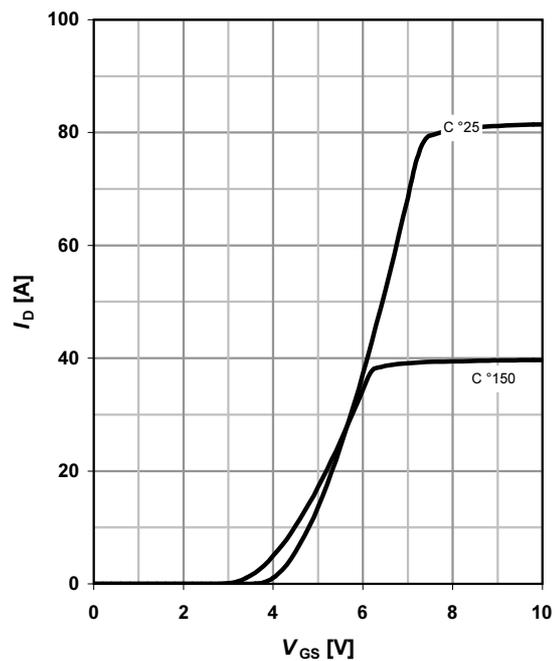$R_{DS(on)}$=f(T_j); I_D=12 A; V_{GS}=10 V

8 Typ. transfer characteristics
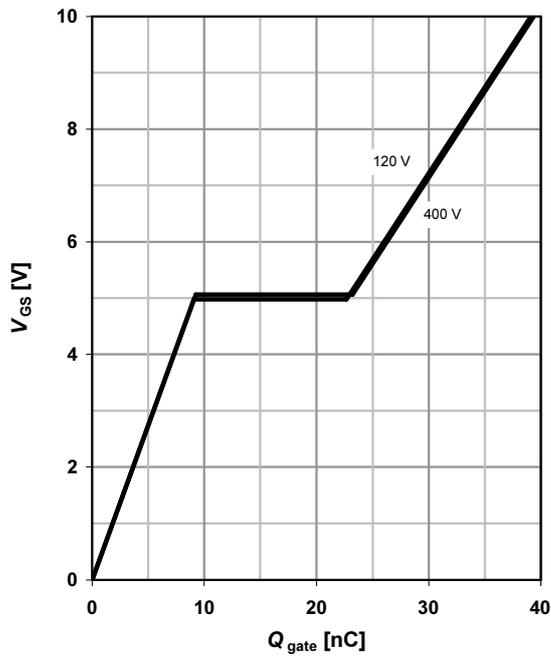
I_D=f(V_{GS}); $|V_{DS}|$>2$|I_D|R_{DS(on)max}$

parameter: T_j

9 Typ. gate charge

V_{GS}=f(Q_{gate}); I_D=12 A pulsed
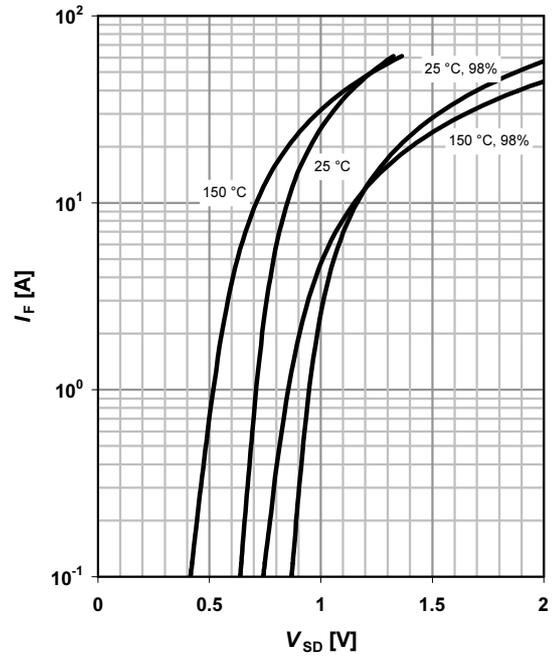
parameter: V_{DD}
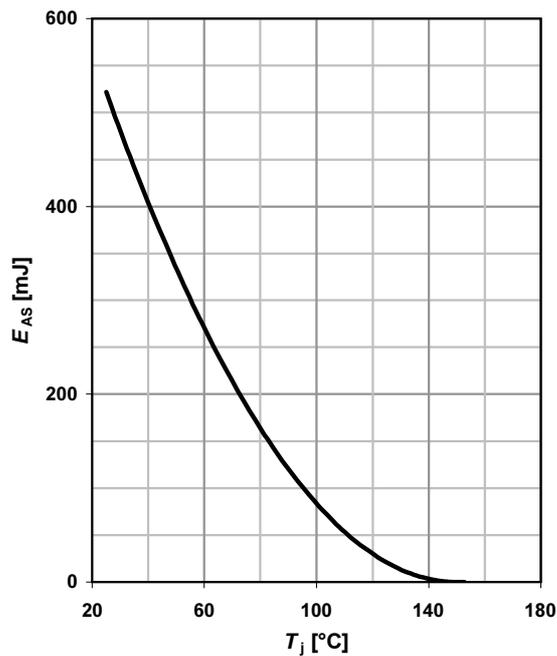

10 Forward characteristics of reverse diode
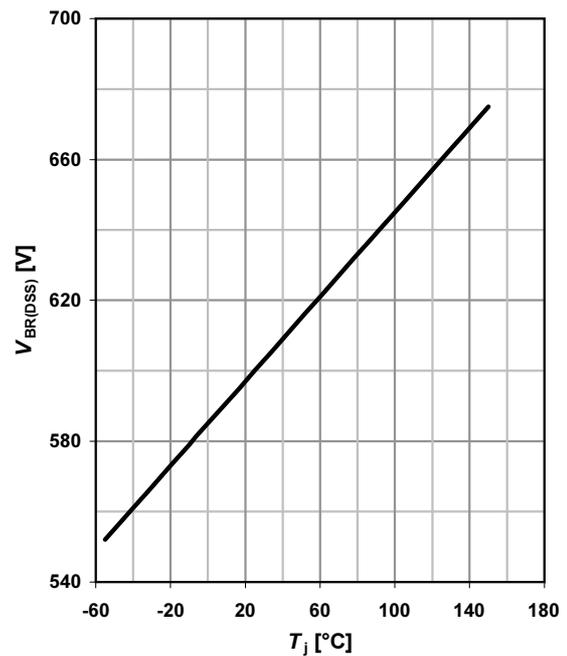
I_F=f(V_{SD})

parameter: T_j

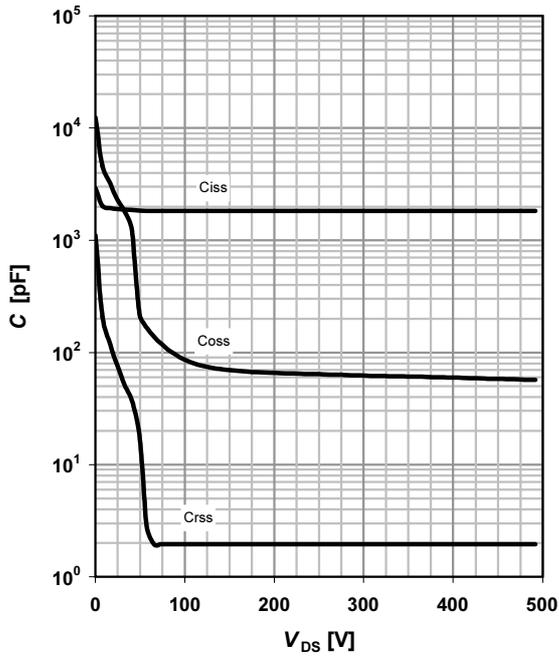**11 Avalanche energy**

E_{AS}=f(T_j); I_D=7.9 A; V_{DD}=50 V

12 Drain-source breakdown voltage
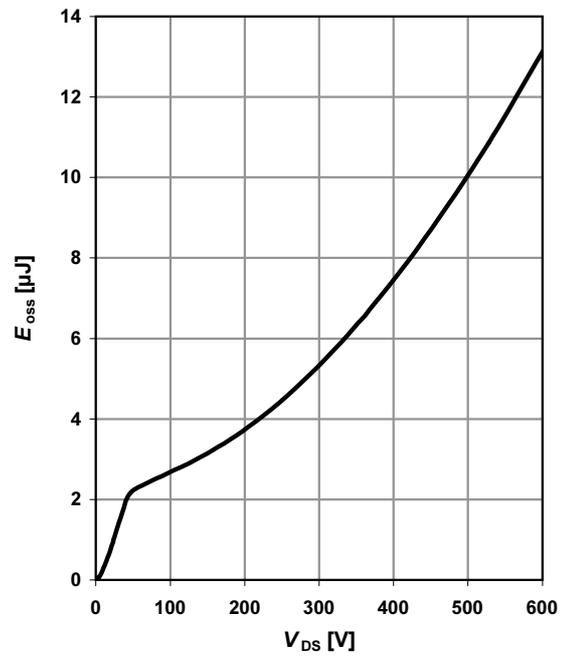
$V_{BR(DSS)}$=f(T_j); I_D=0.25 mA

13 Typ. capacitances

$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz
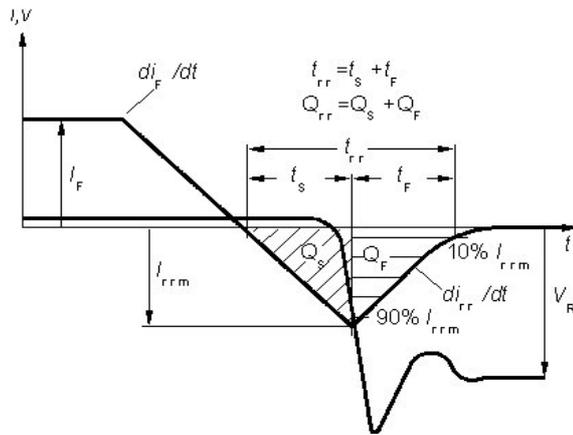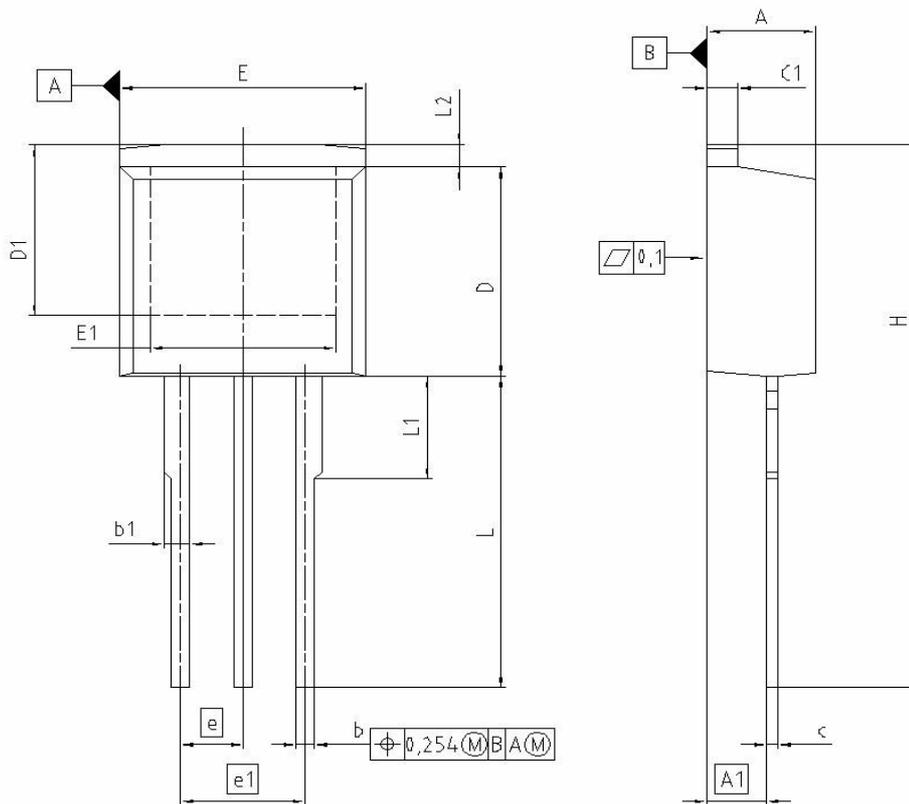
14 Typ. Coss stored energy

$E_{oss} = f(V_{DS})$

Definition of diode switching characteristics

PG-TO262-3-1: Outlines

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.500	0.169	0.177
A1	2.150	2.650	0.085	0.104
b	0.650	0.850	0.026	0.033
b1	0.635	1.400	0.025	0.055
c	0.400	0.600	0.016	0.024
c1	1.170	1.370	0.046	0.054
D	9.050	9.450	0.356	0.372
D1	6.900	7.650	0.272	0.301
E	9.800	10.200	0.386	0.402
E1	7.250	8.600	0.285	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	4.350	4.750	0.171	0.187
L2	0.700	1.300	0.028	0.051

REFERENCE
JEDEC TO262

SCALE

EUROPEAN PROJECTION

ISSUE DATE
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FILE
TO262_1

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- Подбор аналогов;
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- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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